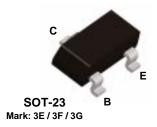


# **BC857A BC857B BC857C**



## **PNP General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 68.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	45	V
V <sub>CBO</sub>	Collector-Base Voltage	50	V
$V_{EBO}$	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	500	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- These ratings are based on a maximum junction temperature of 150 degrees C.
  These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		*BC857A / B / C	
P <sub>D</sub>	Total Device Dissipation	350	mW
	Derate above 25°C	2.8	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

## **PNP General Purpose Amplifier**

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	11 GHALA	cteristic	

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	45		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_{C} = 10  \mu A, I_{E} = 0$	50		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 1.0  \mu A,  I_C = 0$	5.0		V
I <sub>CBO</sub>	Collector-Cutoff Current	V <sub>CB</sub> = 30 V		15	nA
		$V_{CB} = 30 \text{ V}, T_A = 150^{\circ}\text{C}$		4.0	μΑ

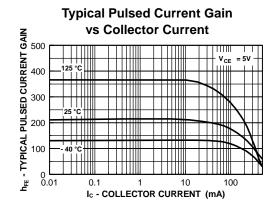
### ON CHARACTERISTICS

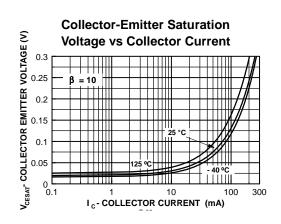
h <sub>FE</sub>	DC Current Gain	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$			
		BC857A	125	250	
		BC857B	220	475	
		BC857C	420	800	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.3	V
3_(34.4)		$I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$		0.65	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$	0.6	0.75	V
(-,		$I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$		0.82	V

### SMALL SIGNAL CHARACTERISTICS

f <sub>T</sub>	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 mHz	100		MHz
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		4.5	pF
NF	Noise Figure	$I_C = 0.2 \text{ mA}, V_{CE} = 5.0,$ $R_S = 2.0 \text{ k}\Omega, f = 1.0 \text{ kHz},$ BW = 200  Hz		10	dB

## **Typical Characteristics**

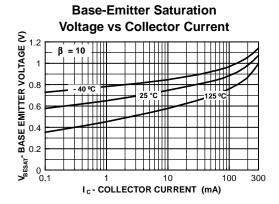


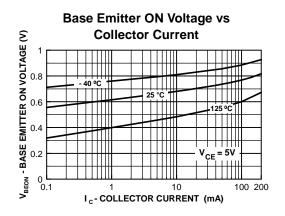


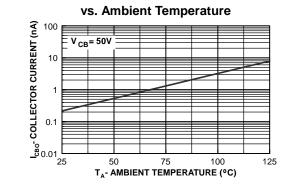
## **PNP General Purpose Amplifier**

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## Typical Characteristics (continued)

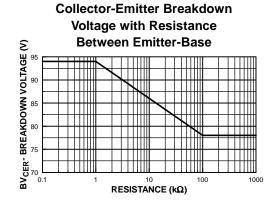


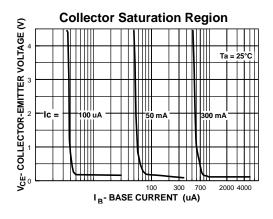


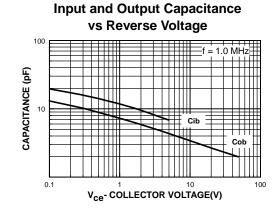


T<sub>A</sub>- AMBIENT TEMPERATURE (°C)

**Collector-Cutoff Current** 



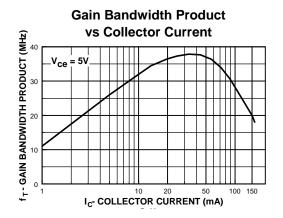


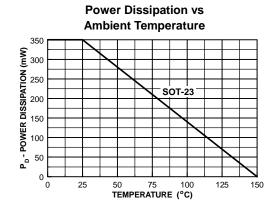


## **PNP General Purpose Amplifier**

(continued)

## Typical Characteristics (continued)





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